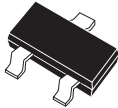


CMPT930

NPN SILICON TRANSISTOR



SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPT930 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose amplifier applications.

Marking Code is C1X.

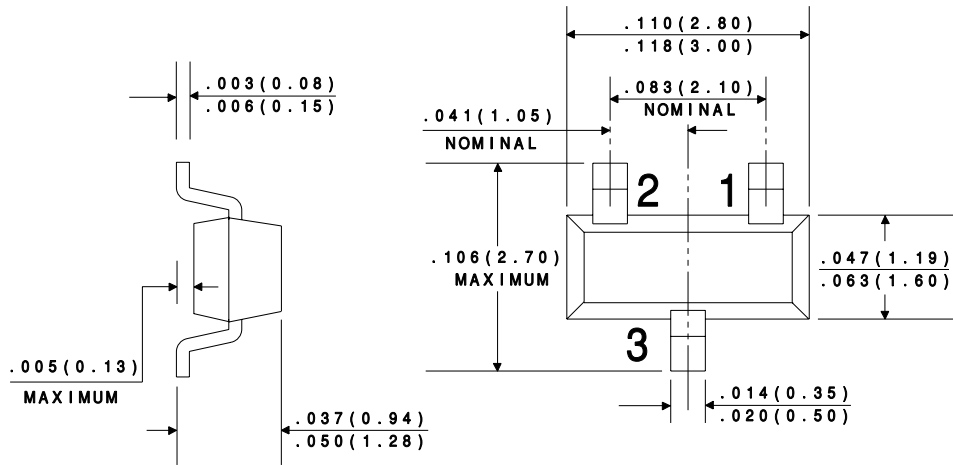
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	45	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	30	mA
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =45V		10	nA
I _{CEO}	V _{CE} =5.0V		10	nA
I _{CES}	V _{CE} =45V		10	nA
I _{EBO}	V _{EB} =5.0V		10	nA
BV _{CBO}	I _C =10μA	45		V
BV _{CEO}	I _C =10mA	45		V
BV _{EBO}	I _E =10μA	5.0		V
V _{CE(SAT)}	I _C =10mA, I _B =0.5mA		1.0	V
V _{BE(SAT)}	I _C =10mA, I _B =0.5mA	0.6	1.0	V
h _{FE}	V _{CE} =5.0V, I _C =10μA	100	300	
h _{FE}	V _{CE} =5.0V, I _C =500μA	150		
h _{FE}	V _{CE} =5.0V, I _C =10mA		600	
f _T	V _{CE} =5.0V, I _C =500mA, f=30MHz	30		MHz
C _{ob}	V _{CB} =5.0V, I _E =0, f=1.0MHz		8.0	pF
NF	V _{CE} =5.0V, I _C =10mA, R _S =10kΩ, f=10Hz to 15.7kHz		3.0	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR